



GENERAL DESCRIPTION

Passivated high commutation triacs in a plastic envelope intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. These devices will commute the full rated rms current at the maximum rated junction temperature without the aid of a snubber.

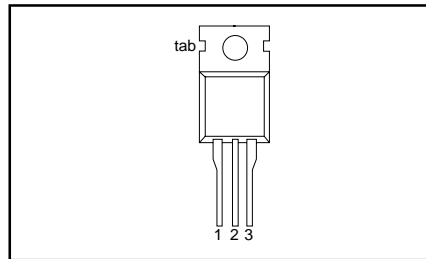
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{DRM}	Repetitive peak off-state voltages	500D 500C 500	600E 600F 600	800B 800C 800	V
$I_{T(RMS)}$	RMS on-state current	4	4	4	A
I_{TSM}	Non-repetitive peak on-state current	25	25	25	A

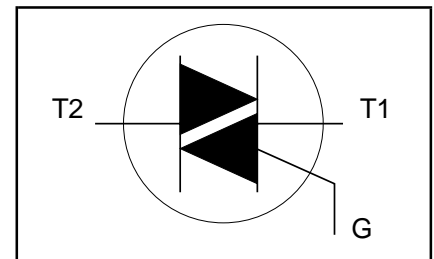
PINNING - TO220AB

PIN	DESCRIPTION
1	main terminal 1
2	main terminal 2
3	gate
tab	main terminal 2

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
				-500 500 ¹	-600 600 ¹	-800 800	
V_{DRM}	Repetitive peak off-state voltages		-				V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107^\circ\text{C}$	-	4			A
I_{TSM}	Non-repetitive peak on-state current	full sine wave; $T_j = 25^\circ\text{C}$ prior to surge	-	25			A
I^2t	I^2t for fusing	$t = 20\text{ ms}$	-	27			A
dl_T/dt	Repetitive rate of rise of on-state current after triggering	$t = 10\text{ ms}$	-	3.1			A ² s
I_{GM}	Peak gate current	$I_{TM} = 6\text{ A}; I_G = 0.2\text{ A}; dl_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100			A/ μs
V_{GM}	Peak gate voltage		-	2			A
P_{GM}	Peak gate power		-	5			V
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	5			W
T_{stg}	Storage temperature		-40	0.5			W
T_j	Operating junction temperature		-	150			$^\circ\text{C}$
				125			$^\circ\text{C}$

¹ Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/ μs .

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	full cycle	-	-	3.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	half cycle in free air	-	-	3.7	K/W
			-	60	-	K/W

STATIC CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

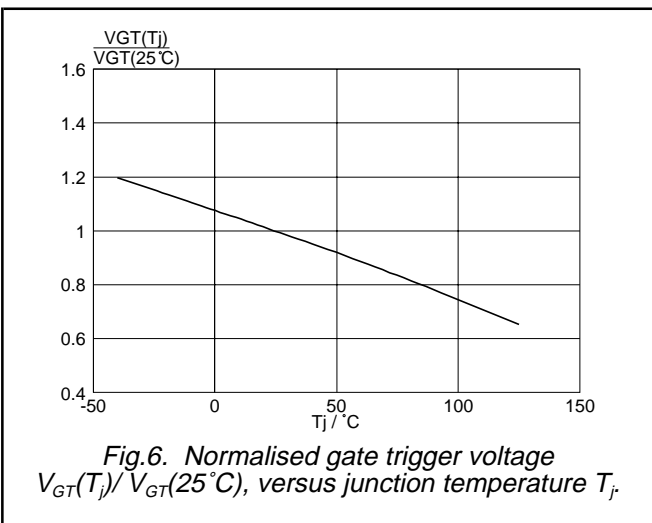
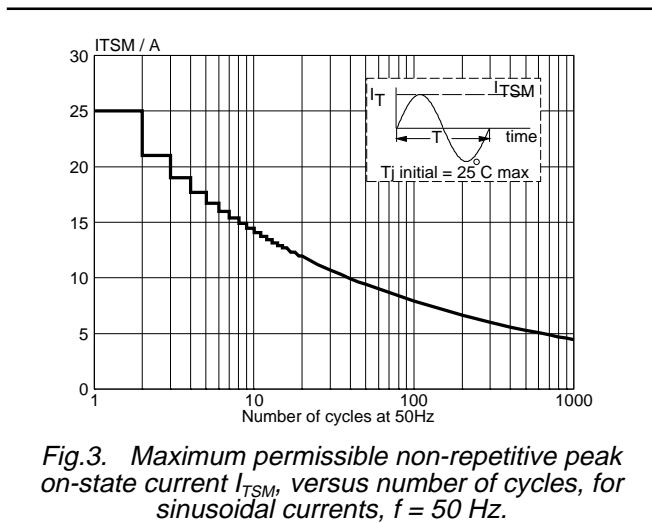
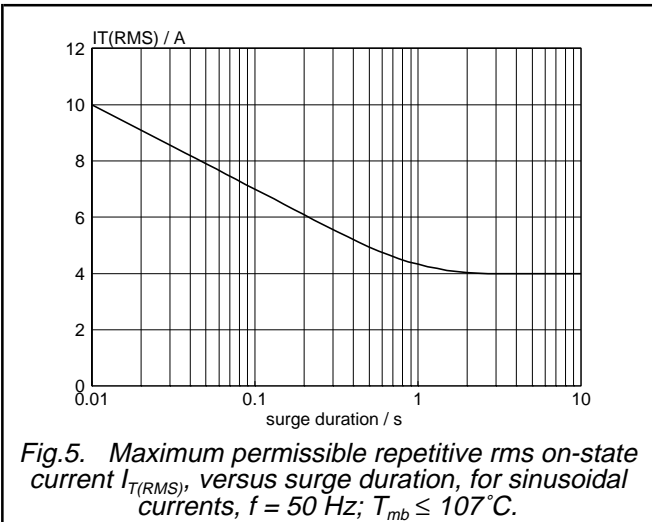
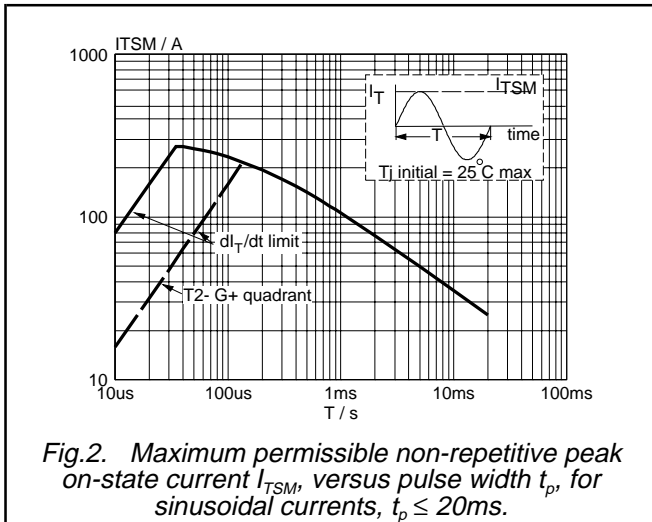
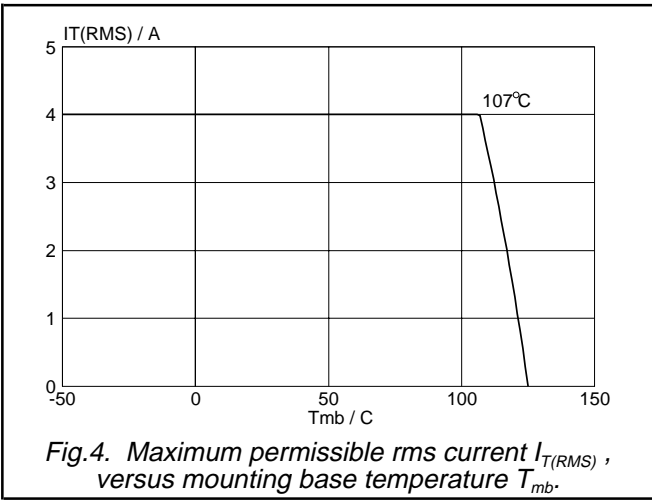
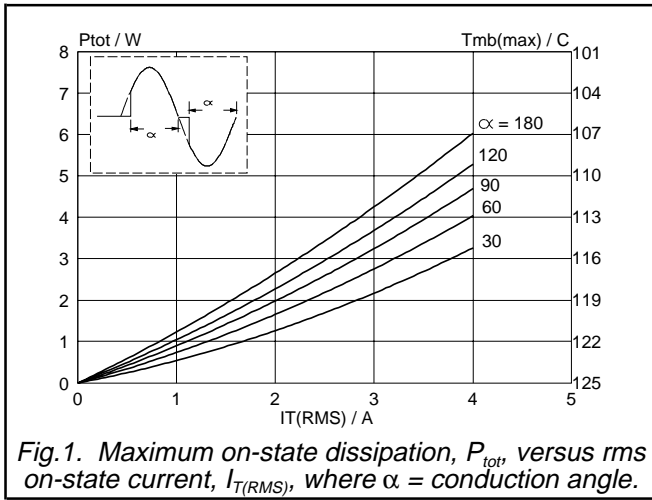
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
		BTA204-			...B	...C
I_{GT}	Gate trigger current ²	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	-	50	35
			-	-	50	35
			-	-	50	35
I_L	Latching current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G-	-	-	30	20
			-	-	45	30
			-	-	30	20
I_H	Holding current	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	-	-	30	20
V_T	On-state voltage	$I_T = 5\text{ A}$	-	1.4	1.7	
V_{GT}	Gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$ $V_D = 400\text{ V}; I_T = 0.1\text{ A};$ $T_j = 125\text{ }^\circ\text{C}$	-	0.7	1.5	
			0.25	0.4	-	
I_D	Off-state leakage current	$V_D = V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	

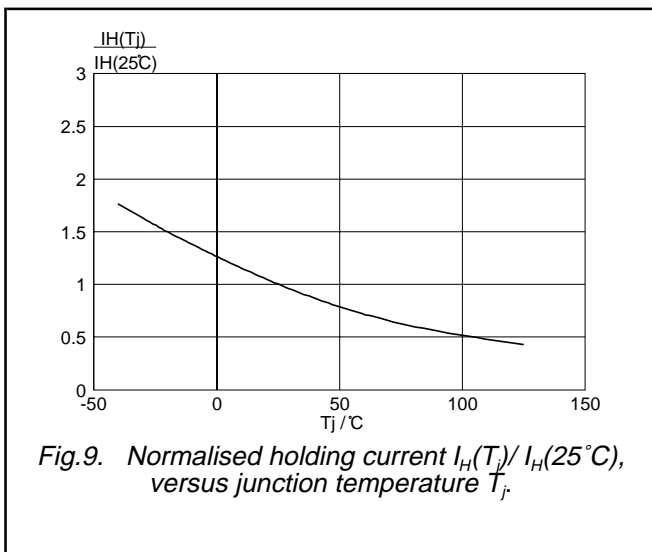
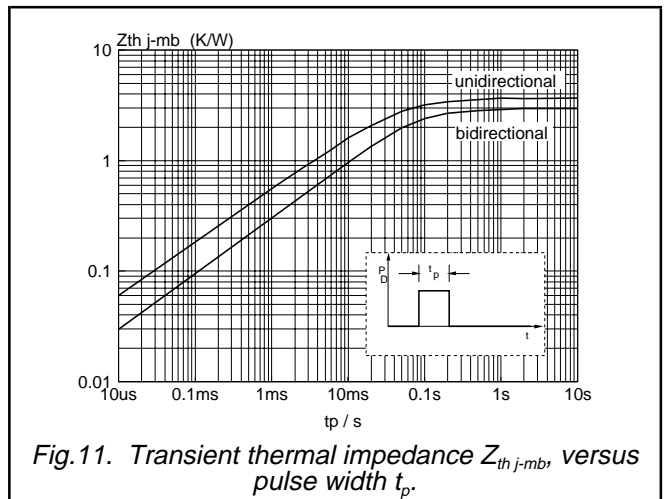
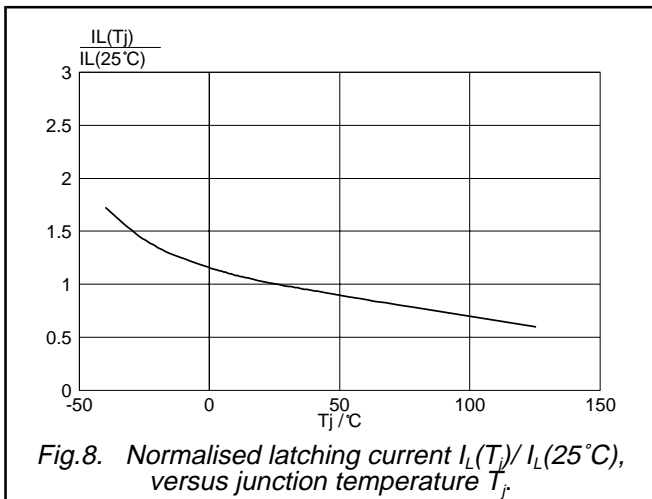
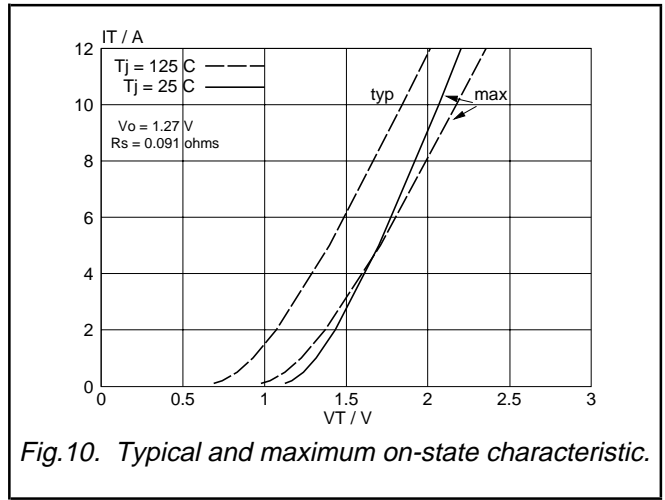
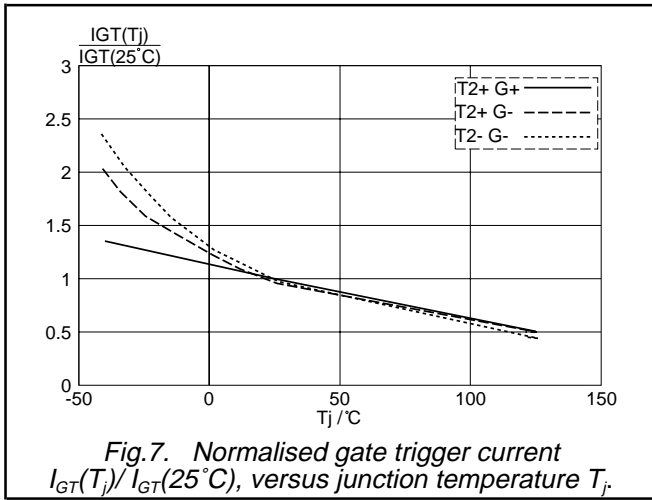
DYNAMIC CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	UNIT	
		BTA204-			...B	...C
dV_D/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}; T_j = 125\text{ }^\circ\text{C};$ exponential waveform; gate open circuit	1000	1000	-	V/ μs
dI_{com}/dt	Critical rate of change of commutating current	$V_{DM} = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{T(RMS)} = 4\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ gate open circuit	6	3	-	A/ms
t_{gt}	Gate controlled turn-on time	$I_{TM} = 12\text{ A}; V_D = V_{DRM(max)}; I_G = 0.1\text{ A};$ $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	-	2	μs

² Device does not trigger in the T2-, G+ quadrant.





MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

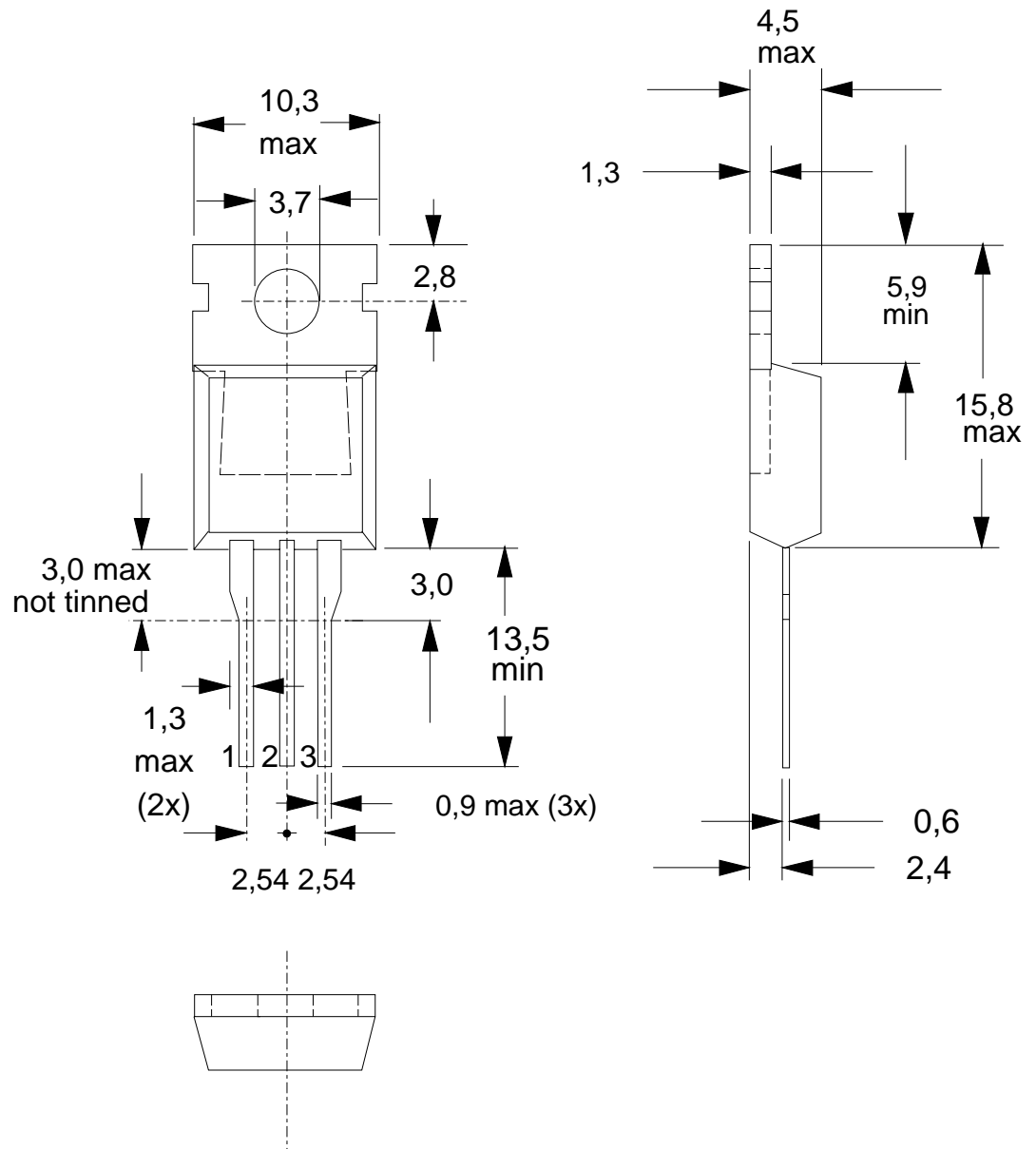


Fig.12. SOT78 (TO220AB). pin 2 connected to mounting base.

Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".